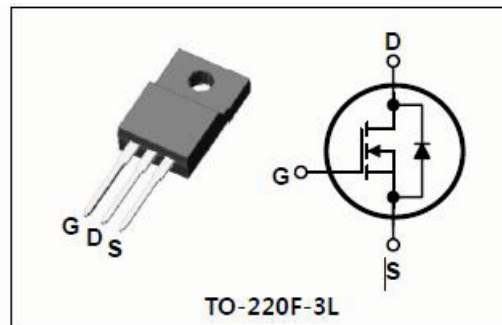


**SWITCHING REGULATOR APPLICATIONS**
**PIN Connection**
**Features**

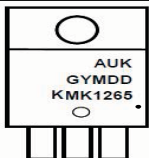
- High Voltage :  $BV_{DSS}=650V(\text{Min.})$
- Low  $C_{rss}$  :  $C_{rss}=14.6pF(\text{Typ.})$
- Low gate charge :  $Q_g=41nC(\text{Typ.})$
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.8\Omega(\text{Max.})$


**Ordering Information**

Type NO.	Marking	Package Code
KMK1265F	KMK1265.	TO-220F-3L

• Dalian

**Marking Diagram**

	Column 1 : Manufacturer Column 2 : Production Information e.g.) GYMDD -. G : Factory management code -. YMDD : Date Code (year, month, date) Column 3 : Device Code
-------------------------------------------------------------------------------------	------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------

**Absolute maximum ratings ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Ratings	Unit	
Drain-source voltage	$V_{DSS}$	650	V	
Gate-source voltage	$V_{GS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_c=25^\circ\text{C}$	12	A
		$T_c=100^\circ\text{C}$	4.5	A
Drain current (pulsed) *	$I_{DM}$	48	A	
Power dissipation	$P_D$	45	W	
Avalanche current (single) ②	$I_{AS}$	12	A	
Single pulsed avalanche energy ②	$E_{AS}$	140	mJ	
Avalanche current (Repetitive) ①	$I_{AR}$	12	A	
Repetitive avalanche energy ①	$E_{AR}$	7.6	mJ	
Junction temperature	$T_J$	150	$^\circ\text{C}$	
Storage temperature range	$T_{stg}$	$-55 \sim 150$		

\* : Limited by maximum junction temperature

此规格如果需要申请样品, 请联络

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Characteristic	Symbol	Typ.	Max	Unit
Thermal resistance	Junction-case	-	2.7	$^\circ\text{C}/\text{W}$
	Junction-ambient	-	62.5	

# KMK1265F

## Electrical Characteristics (Tc=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0	650	-	-	V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	2.0	-	4.0	V
Drain-source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	-	-	1	μA
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
Drain-source on-resistance ④	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =6.0A	-	0.68	0.80	Ω
Forward transfer conductance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V I <sub>D</sub> =6.0A	-	10	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V F=1MHz	-	2162	2882	pF
Output capacitance	C <sub>oss</sub>		-	183	244	
Reverse transfer capacitance	C <sub>rss</sub>		-	14.6	19.4	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =300V, I <sub>D</sub> =12A R <sub>G</sub> =25Ω ③④	-	30	-	ns
Rise time	t <sub>r</sub>		-	85	-	
Turn-off delay time	t <sub>d(off)</sub>		-	140	-	
Fall time	t <sub>f</sub>		-	90	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =520V, V <sub>GS</sub> =10V I <sub>D</sub> =12A ③④	-	43	65	nC
Gate-source charge	Q <sub>gs</sub>		-	13	-	
Gate-drain charge	Q <sub>gd</sub>		-	10.5	-	

## Source-Drain Diode Ratings and Characteristics(Tc=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Source current(DC)	I <sub>s</sub>	Integral reverse diode in the MOSFET	-	-	12	A
Source current(pulsed) ①	I <sub>SM</sub>		-	-	48	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>s</sub> =12A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>s</sub> =12A, V <sub>GS</sub> =0V dI <sub>F</sub> /dt=100A/us	-	500	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	4.3	-	uC

Note:

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=1.8mH, I<sub>s</sub>=12A, V<sub>m</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
- ③ Pulse Test : Pulse width≤300us, Duty cycle≤2%
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

Fig. 1  $I_D - V_{DS}$

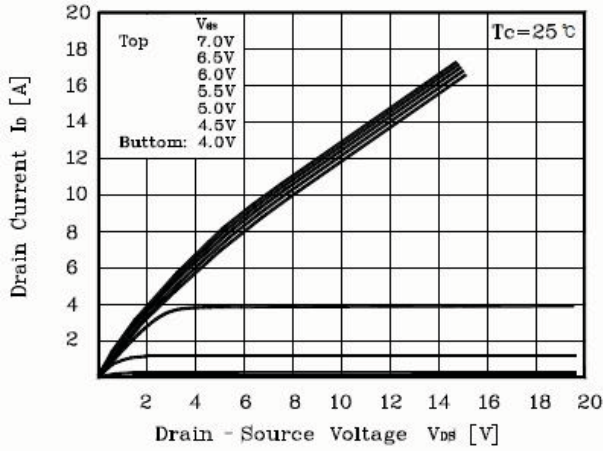


Fig. 2  $I_D - V_{GS}$

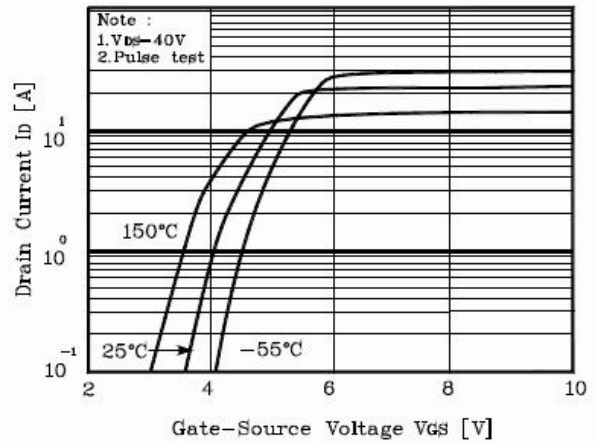


Fig. 3  $R_{DS(on)} - I_D$

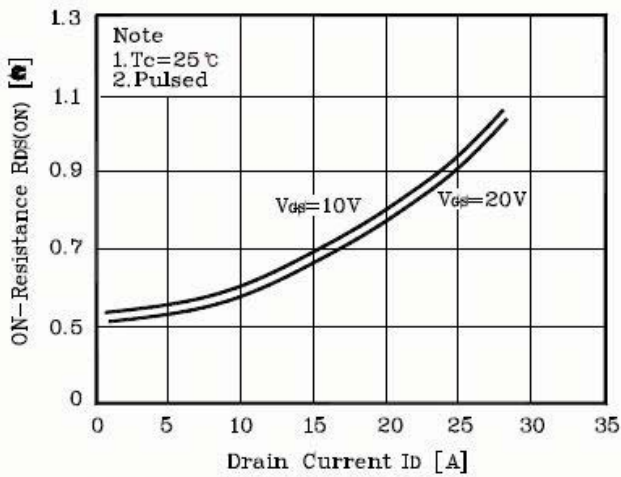


Fig. 4  $I_S - V_{SD}$

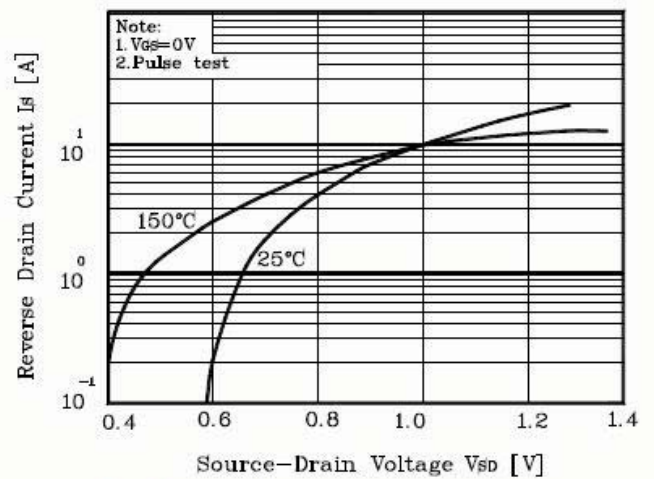


Fig. 5 Capacitance -  $V_{DS}$

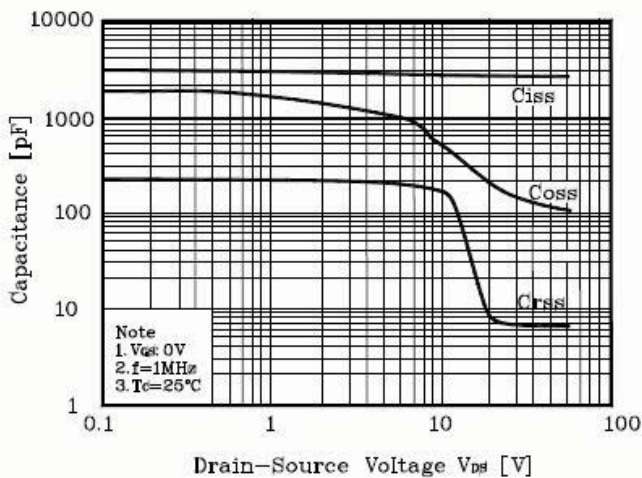
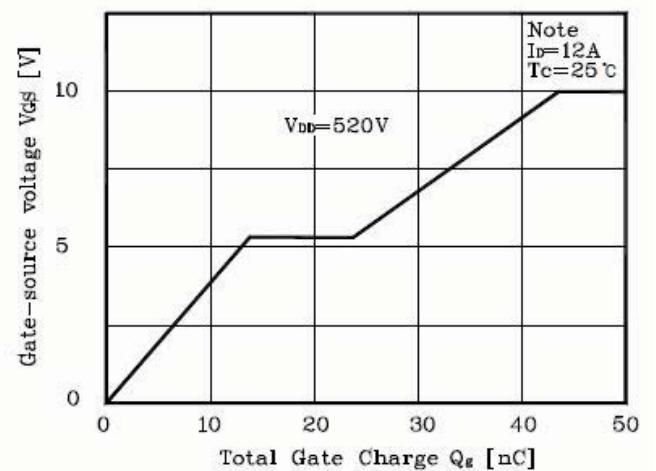


Fig. 6  $V_{GS} - Q_g$



## Electrical Characteristic Curves

Fig. 7  $V_{DSS} - T_J$

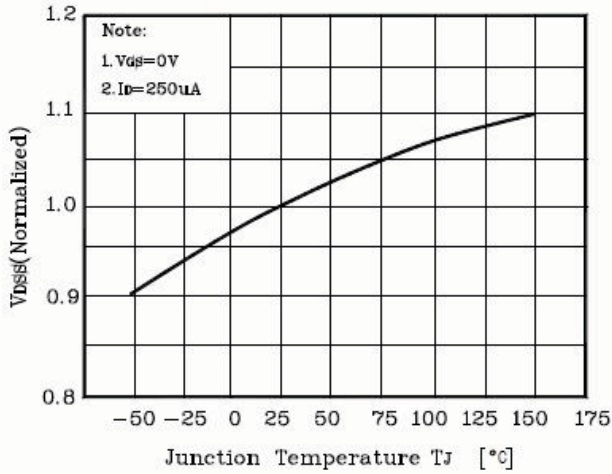


Fig.8  $R_{DS(on)} - T_J$

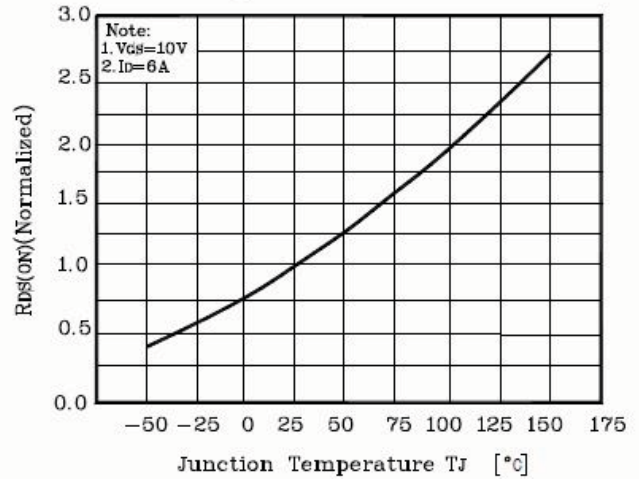


Fig. 9  $I_D - T_C$

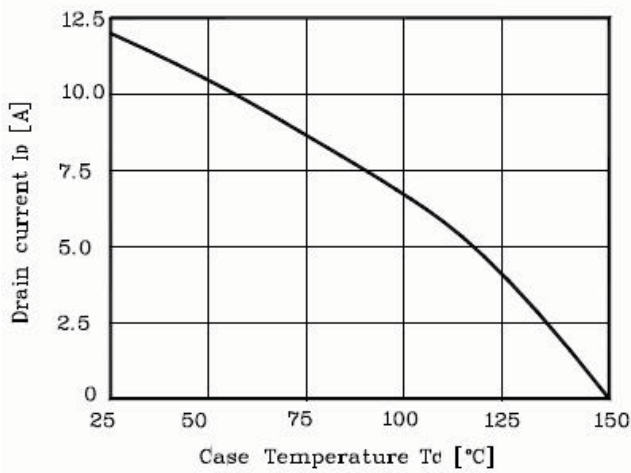


Fig. 10 Safe Operating Area

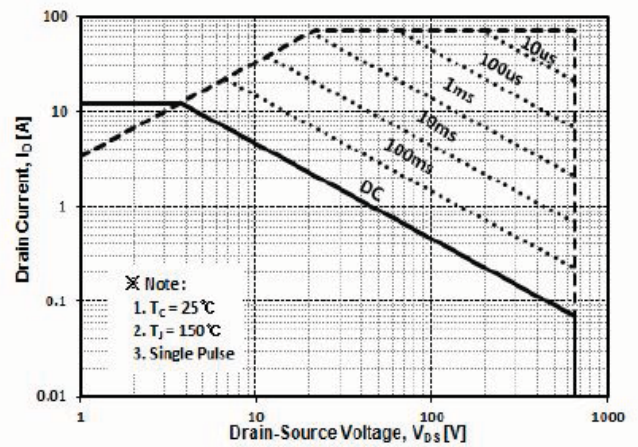


Fig. 11 Gate Charge Test Circuit & Waveform

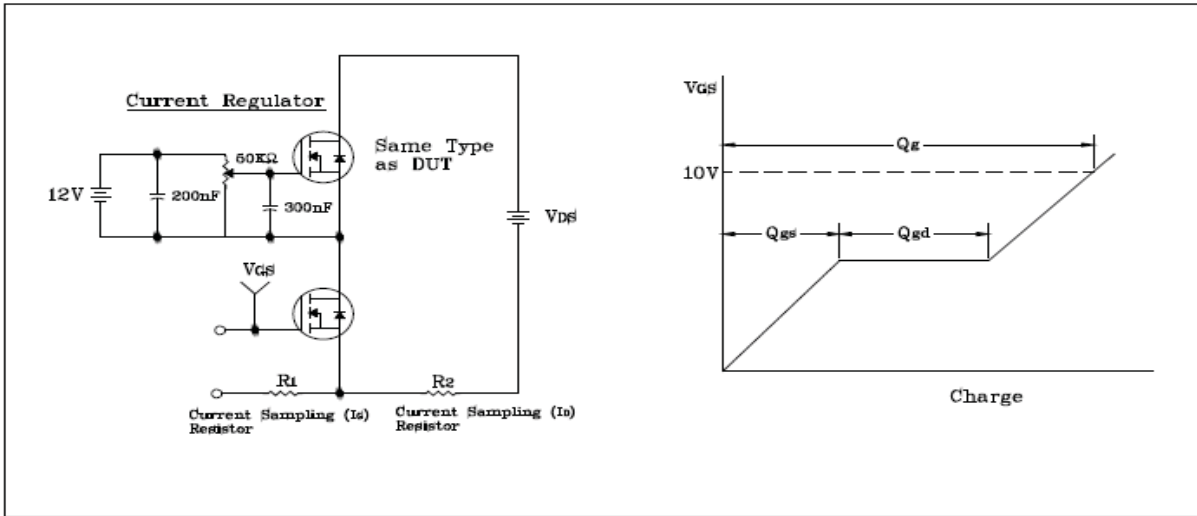


Fig. 12 Resistive Switching Test Circuit & Waveform

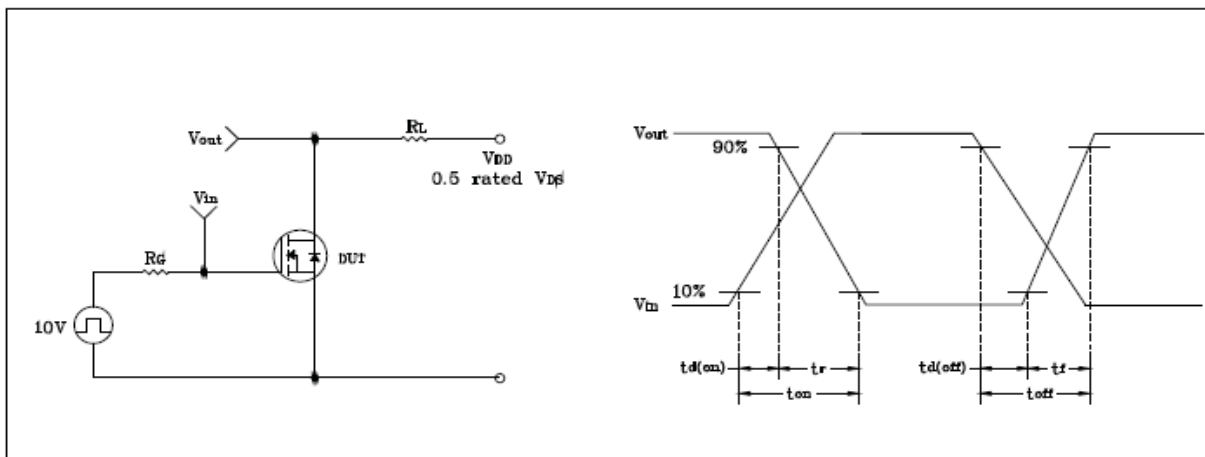


Fig. 13 EAs Test Circuit & Waveform

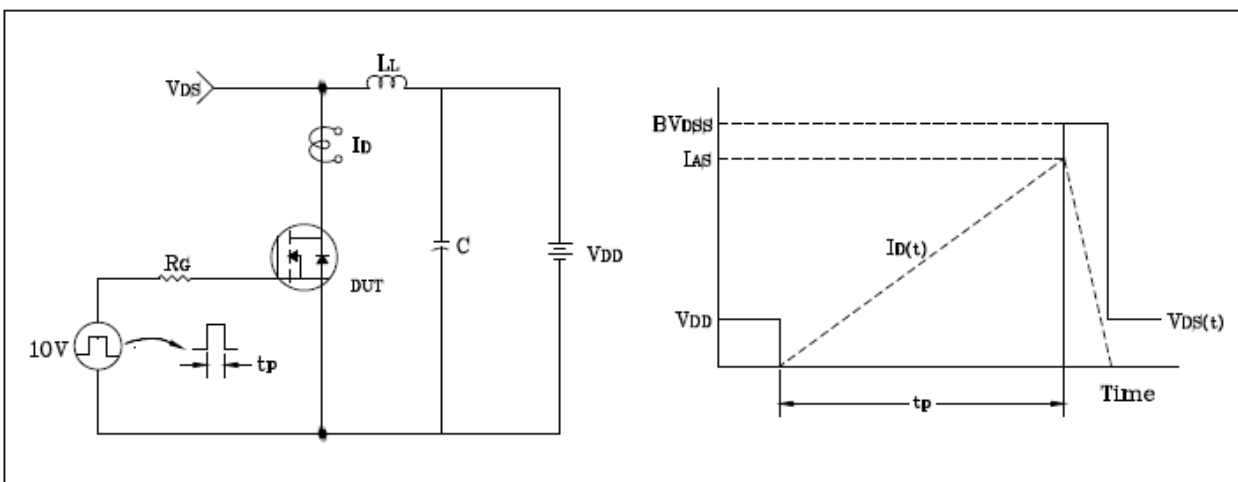
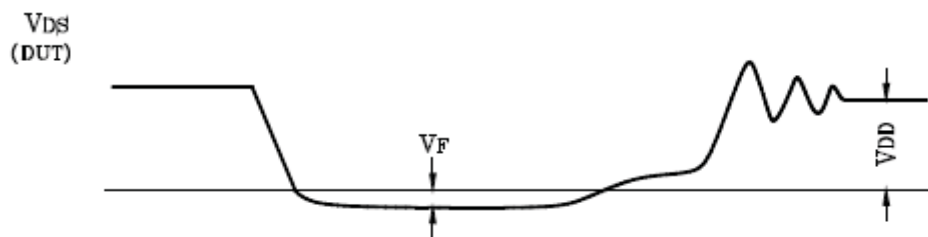
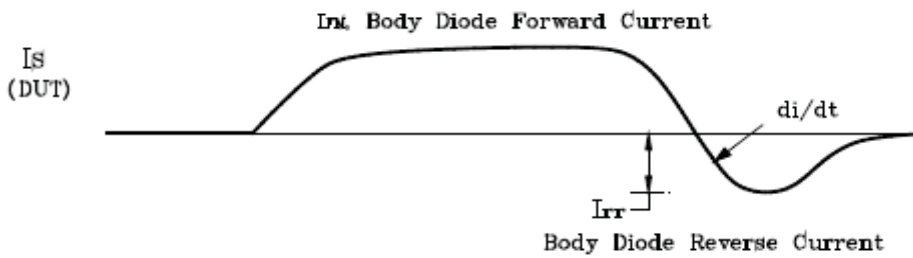
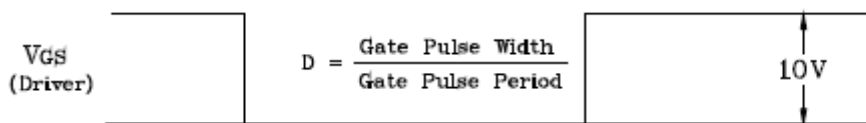
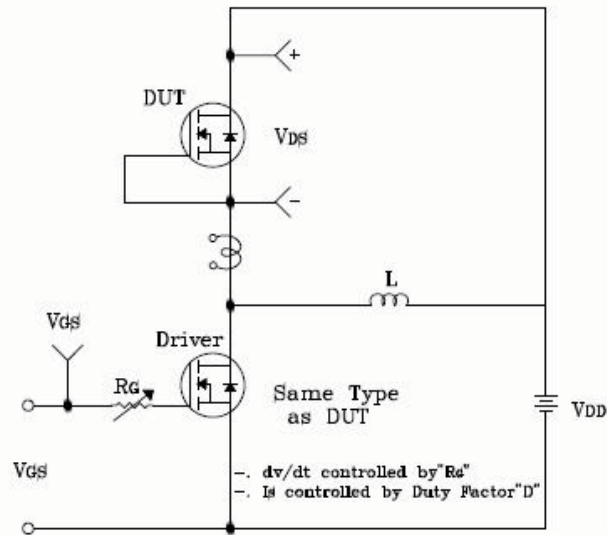


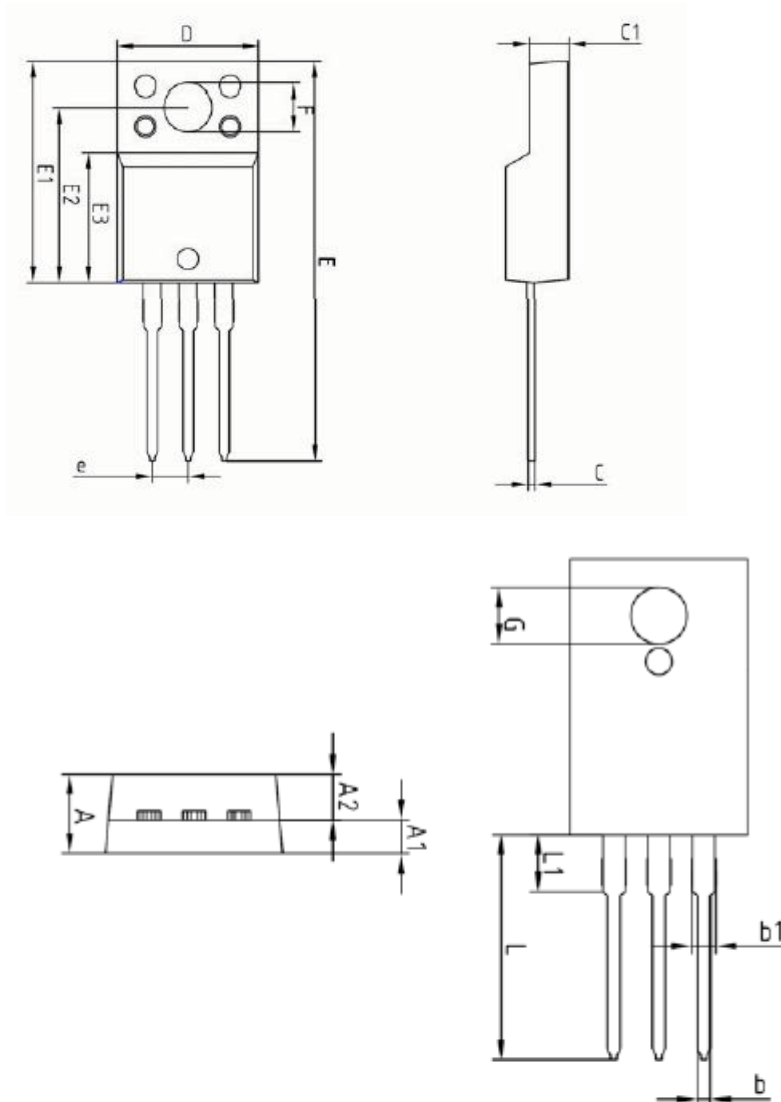
Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



# KMK1265F

## Outline Dimension

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	-	-	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	-	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	2.54 BSC			
L	12.40	-	13.00	
L1	3.46 BSC			



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